

IN THE CLAIMS

1. (Original) A semiconductor optical device, comprising:
 - an InP substrate;
 - an active region formed above the InP substrate, said active region being comprised of a quantum well structure;
 - optical guiding layers each formed on and under said active region; and
 - clad layers;

wherein on sides in the direction crossing the light-emitting direction, the sides of the active region are buried with semiconductor layers having band gap energy greater than that of a quantum well layer; and

wherein a composition of Al of the quantum well layer is in the group consisting of InGaAlAs compound semiconductor layers, a composition ratio of the Al being in the range of 0 to 0.13, both inclusive.
2. (Original) The semiconductor optical device according to claim 1, wherein a composition ratio of Al of the quantum well layer is in the range of 0.01 to 0.1, both inclusive.
3. (Original) The semiconductor optical device according to claim 1, wherein the InGaAlAs is in the group consisting of compositions A (In: 0.87, Ga: 0, Al: 0.13), B (In: 1.0, Ga: 0, Al: 0), C (In: 0, Ga: 1.0, Al: 0), and D (In: 0, Ga: 0.87, Al: 0.13) in the composition diagram of the four-element based compound semiconductor materials ($In_{1-x-y}Ga_xAl_yAs$).
4. (Original) A semiconductor optical device, comprising:
 - an InP substrate;
 - an active region formed above the InP substrate, said active region being comprised of a quantum well structure;
 - optical guiding layers each formed on and under said active region; and
 - clad layers;

wherein on sides in the direction crossing the light-emitting direction, the sides

of the active region are buried with semiconductor layers having band gap energy greater than that of a quantum well layer;

wherein the composition ($In_{1-x-y}Ga_xAl_yAs$) of the quantum well layer is in the group consisting of compositions E (In: 0.52, Ga: 0, Al: 0.48), F (In: 0.53, Ga: 0.47, Al: 0), C (In: 0, Ga: 1.0, Al: 0), and G (In: 0, Ga: 0, Al: 1.0) in the composition diagram of the four-element based compound semiconductor materials; and

wherein the quantum well layer has tensile strain.

5. (Original) The semiconductor optical device according to claim 1, wherein the InGaAlAs layer is in the group consisting of compositions H (In: 0.53, Ga: 0.34, Al: 0.13), F (In: 0.53, Ga: 0.47, Al: 0), C (In: 0, Ga: 1.0, Al: 0), and D (In: 0, Ga: 0.87, Al: 0.13) in the composition diagram of the four-element based compound semiconductor materials ($In_{1-x-y}Ga_xAl_yAs$), and has tensile strain.
6. (Original) The semiconductor optical device according to claim 5, wherein the photoluminescence wavelength from the active region is within the range of 1.25 .m to 1.35.m.
7. (Original) The semiconductor optical device according to claim 5, wherein the InGaAlAs layer is in the group consisting of compositions H (In: 0.53, Ga: 0.34, Al: 0.13), I (In: 0.53, Ga: 0.4, Al: 0.07), J (In: 0.4, Ga: 0.6, Al: 0), K (In: 0.26, Ga: 0.74, Al: 0) and L (In: 0.46, Ga: 0.41, Al: 0.13) in the composition diagram of the four-element based compound semiconductor materials ($In_{1-x-y}Ga_xAl_yAs$); and has tensile strain.
8. (Original) The semiconductor optical device according to claim 5, wherein the photoluminescence wavelength from the active region is within the range of 1.25 .m to 1.35.m; and wherein the InGaAlAs layer is in the group consisting of compositions H (In: 0.53, Ga: 0.34, Al: 0.13), I (In: 0.53, Ga: 0.4, Al: 0.07), J (In: 0.4, Ga: 0.6, Al: 0), K (In: 0.26, Ga: 0.74, Al: 0) and L (In: 0.46, Ga: 0.41, Al: 0.13) in the composition diagram of the four-element based compound semiconductor materials ($In_{1-x-y}Ga_xAl_yAs$); and has tensile strain.

y Ga_xAl_yAs).

9. (Original) The semiconductor optical device according to claim 6, wherein
a barrier layer constituting the active region is p-type doped.
10. (Original) The semiconductor optical device according to claim 7, wherein
a barrier layer constituting the active region is p-type doped.
11. (Original) The semiconductor optical device according to claim 8, wherein
a barrier layer constituting the active region is p-type doped.
12. (Original) The semiconductor optical device according to claim 1, wherein
the photoluminescence wavelength from the active region is within the range
of 1.36 .m to 1.49.m.
13. (Original) The semiconductor optical device according to claim 1, wherein
the InGaAlAs layer is in the group consisting of compositions O (In: 0.76, Ga:
0.11, Al: 0.13), P (In: 0.5, Ga: 0.5, Al: 0), Q (In: 0.34, Ga: 0.66, Al: 0), and R (In:
0.55, Ga: 0.32, Al: 0.13) in the composition diagram of the four-element based
compound semiconductor materials ($In_{1-x-y}Ga_xAl_yAs$).
14. (Original) The semiconductor optical device according to claim 1,
wherein the InGaAlAs layer is in the group consisting of the compositions O
(In: 0.76, Ga: 0.11, Al: 0.13), P (In: 0.5, Ga: 0.5, Al: 0), Q (In: 0.34, Ga: 0.66, Al: 0),
and R (In: 0.55, Ga: 0.32, Al: 0.13) in the composition diagram of the four-element
based compound semiconductor materials ($In_{1-x-y}Ga_xAl_yAs$); and
wherein the photoluminescence wavelength from the active region is within
the range of 1.36 .m to 1.49.m.
15. (Original) The semiconductor optical device according to claim 12, wherein
a barrier layer constituting the active region is p-type doped.

16. (Original) The semiconductor optical device according to claim 13, wherein
a barrier layer constituting the active region is p-type doped.
17. (Original) The semiconductor optical device according to claim 14, wherein
a barrier layer constituting the active region is p-type doped.
18. (Currently amended) An optical module at least including a package substrate and a semiconductor optical device mounted on the package substrate,
wherein said semiconductor optical device is a semiconductor optical device
~~according to any one of claims 1 to 17 comprising: an InP substrate; an active region~~
~~formed above the InP substrate, said active region being comprised of a quantum well~~
~~structure; optical guiding layers each formed on and under said active region; and clad~~
~~layers; wherein on sides in the direction crossing the light-emitting direction, the sides~~
~~of the active region are buried with semiconductor layers having band gap energy~~
~~greater than that of a quantum well layer; and wherein a composition of Al of the~~
~~quantum well layer is in the group consisting of InGaAlAs compound semiconductor~~
~~layers, a composition ratio of the Al being in the range of 0 to 0.13, both inclusive.~~
19. (Original) The optical module according to claim 18,
wherein the sealing structure of the optical module is of non-hermitic sealing;
and
wherein the semiconductor optical device is at least mounted on the package
substrate without using a temperature controller.